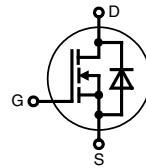


CoolMOS™¹⁾ Power MOSFET in ISOPLUS247™ Package

N-Channel Enhancement Mode
Low $R_{DS(on)}$, High V_{DSS} MOSFET
Package with Electrically Isolated Base

$I_{D25} = 25\text{ A}$
 $V_{DSS} = 800\text{ V}$
 $R_{DS(on)} = 125\text{ m}\Omega$



ISOPLUS 247™



G = Gate, D = Drain, S = Source

MOSFET

Symbol	Conditions	Maximum Ratings		
V_{DSS}	$T_{VJ} = 25^\circ\text{C}$ to 150°C	800		V
V_{GS}		± 20		V
I_{D25}	$T_C = 25^\circ\text{C}$	25		A
I_{D90}	$T_C = 90^\circ\text{C}$	18		A
dv/dt	$V_{DS} < V_{DSS}$; $I_F \leq 17\text{ A}$ $di_F/dt \leq 100\text{ A}/\mu\text{s}$ $T_{VJ} = 150^\circ\text{C}$	6	V/ns	
E_{AS}	$I_D = 4\text{ A}$; $L = 80\text{ mH}$; $T_C = 25^\circ\text{C}$	0.67		mJ
E_{AR}	$I_D = 17\text{ A}$; $L = 3.3\text{ mH}$; $T_C = 25^\circ\text{C}$	0.5		mJ

Symbol	Conditions	Characteristic Values		
		($T_{VJ} = 25^\circ\text{C}$, unless otherwise specified)	min.	typ.
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$; $I_D = I_{D90}$		125	150
$V_{GS(th)}$	$V_{DS} = 20\text{ V}$; $I_D = 2\text{ mA}$	2		4
I_{DSS}	$V_{DS} = V_{DSS}$; $V_{GS} = 0\text{ V}$; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		100	50
I_{GSS}	$V_{GS} = \pm 20\text{ V}$; $V_{DS} = 0\text{ V}$			200
Q_g Q_{gs} Q_{gd}	$V_{GS} = 10\text{ V}$; $V_{DS} = 640\text{ V}$; $I_D = 34\text{ A}$		180 24 92	355
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	$V_{GS} = 10\text{ V}$; $V_{DS} = 640\text{ V}$ $I_D = 34\text{ A}$; $R_G = 2.2\text{ }\Omega$		25 15 72 6	ns ns ns ns
V_F	(reverse conduction) $I_F = 12.5\text{ A}$; $V_{GS} = 0\text{ V}$		1	1.3
R_{thJC}				0.5
				K/W

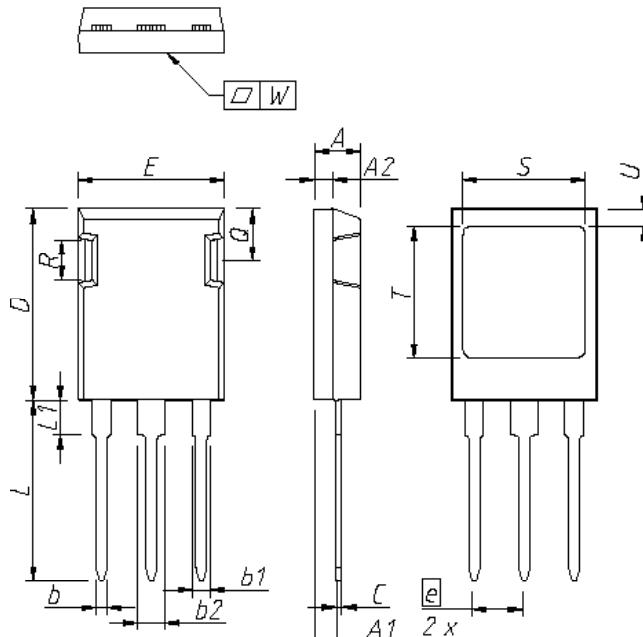
¹⁾ CoolMOS™ is a trademark of Infineon Technologies AG.

Component

Symbol	Conditions	Maximum Ratings		
V_{ISOL}	$I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}$	2500	2500	V~
T_{VJ}		-40...+150	-40...+150	°C
T_{stg}		-40...+125	-40...+125	°C
T_L	1.6 mm from case for 10 s	300	300	°C
F_c	mounting force with clip	20 ... 120	20 ... 120	N

Symbol **Conditions** **Characteristic Values**

Symbol	Conditions	min.	typ.	max.
C_p	coupling capacity bewtween shorted pin and mounting tab in the case		30	pF
R_{thCH}	with heatsink compound		0.25	K/W
Weight		6		g



DIM.	MILLIMETER		INCHES	
	MIN	MAX	MIN	MAX
A	4,83	5,21	0,190	0,205
A1	2,29	2,54	0,090	0,100
A2	1,91	2,16	0,075	0,085
b	1,14	1,40	0,045	0,055
b1	1,91	2,15	0,075	0,085
b2	2,92	3,20	0,115	0,126
C	0,61	0,83	0,024	0,033
D	20,80	21,34	0,819	0,840
E	15,75	16,13	0,620	0,635
e	5,45 BSC		0,215 BSC	
L	19,81	20,60	0,780	0,811
L1	3,81	4,38	0,150	0,172
Q	5,59	6,20	0,220	0,244
R	4,32	4,85	0,170	0,191
S	13,21	13,72	0,520	0,540
T	15,75	16,26	0,620	0,640
U	1,65	2,03	0,065	0,080
W	-	0,10	-	0,004

Die konvexe Form des Substrates ist typ. < 0,04 mm über der Kunststoffoberfläche der Bauteilunterseite
The convex bow of substrate is typ. < 0.04 mm over plastic surface level of device bottom side

Die Gehäuseabmessungen entsprechen dem Typ TO-247 AD gemäß JEDEC außer Schraubloch und L_{max} .
This drawing will meet all dimensions requirement of JEDEC outline TO-247 AD except screw hole and except L_{max} .